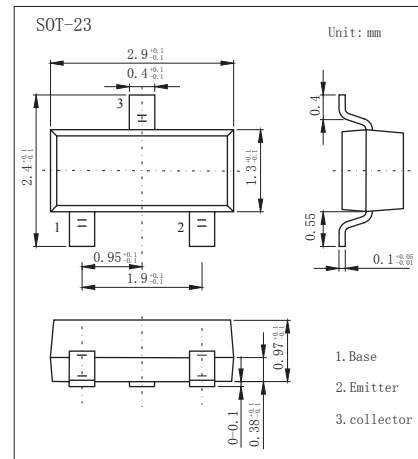


PNP Transistors

KTA1298

■ Features

- Collector Power Dissipation: $P_c=200\text{mW}$
- Collector Current: $I_c=-800\text{mA}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	-35	V
Collector-Base Voltage	V_{CBO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_c	-800	mA
Collector Power Dissipation	P_c	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=-1\text{mA}, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_c=0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_c=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-1\text{V}, I_c=-100\text{mA}$	100		320	
		$V_{CE}=-1\text{V}, I_c=-800\text{mA}$	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=-500\text{mA}, I_B=-20\text{mA}$			-0.4	V
Transition Frequency	f_T	$V_{CE}=-5\text{V}, I_c=-10\text{mA}$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		13		pF

■ h_{FE} Classification

Type	KTA1298-O	KTA1298-Y
Range	100-200	160-320
Marking	KIO	KIY



炬芯微
XUANXINWEI

SMD Type

Transistors

PNP Transistors

KTA1298

■ Typical Characteristics

